

ABSTRACT OF THE DISCLOSURE

There is formed a gate electrode (word line) via a gate insulating film on a semiconductor substrate, the gate electrode extending in the direction inclining at an angle of approximately 45 degrees to the extending direction of an element region. The element region is divided into three portions by the two gate electrodes. In each element region portion, two MOS transistors are provided. A bit line is connected to a W plug provided in the central region portion and lower electrodes of two ferroelectric capacitors are connected to other W plugs provided in both end region portions. The extending direction of the bit line inclines approximately 45 degrees to the extending direction of the element region.